

The D30NA30Z4 is a high performance Aluminum Nitride (AIN) chip attenuator intended as a cost competitive alternative to Beryllium Oxide (BeO). The attenuator is well suited to all cellular frequency bands such as; AMPS, GSM, DCS, PCS, PHS and UMTS. The high power handling makes the part ideal for inter-stage matching, directional couplers, and for use in isolators. The attenuator is also RoHS compliant!

### **Features:**

- RoHS Compliant
- 30 Watts
- Low Cost
- DC 3.0GHz
- AIN Ceramic
- Non-Nichrome Resistive Element
- Low VSWR
- 100% Tested

### **General Specifications**

Resistive Element Thick film
Substrate AIN Ceramic

Terminal Finish Matte Tin over Nickel Barrier

Operating Temperature -55 to +200°C (see de rating chart)

Tolerance is  $\pm 0.010$ ", unless otherwise specified. Designed to meet or exceed applicable portions of MIL-E-5400. **All dimensions in inches.** 

#### **Electrical Specifications**

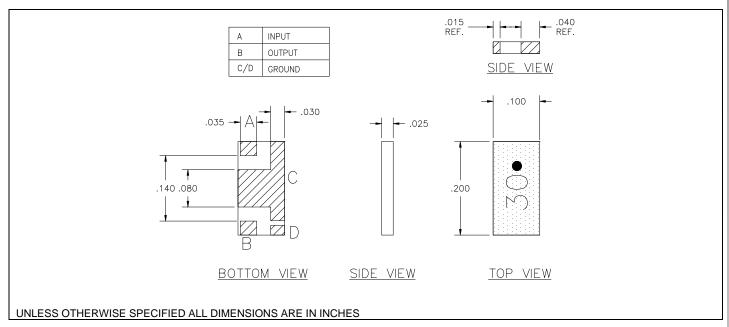
**Attenuation Value:** 30dB +1dB, -1dB; DC - 2.7GHz +1dB, -1.5dB; DC - 3.0GHz

Power: 30 Watts
Frequency Range: DC - 3.0GHz

Input Return Loss: 20dB
Specification based on unit properly installed using suggested m

Specification based on unit properly installed using suggested mounting instructions and a 50 ohm nominal impedance. **Specifications subject to change.** 

# **Outline Drawing**

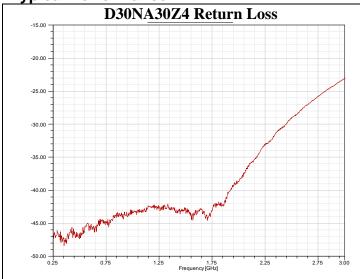


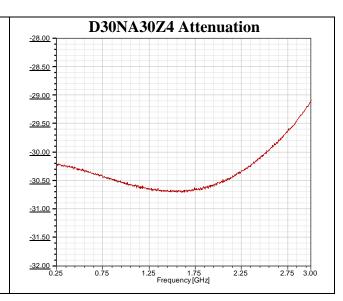


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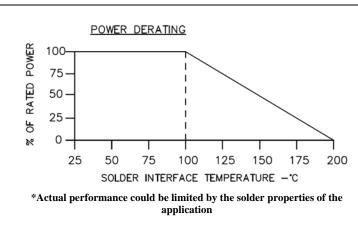


**Typical Performance:** 

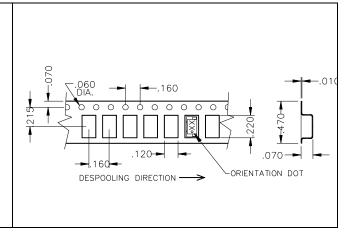




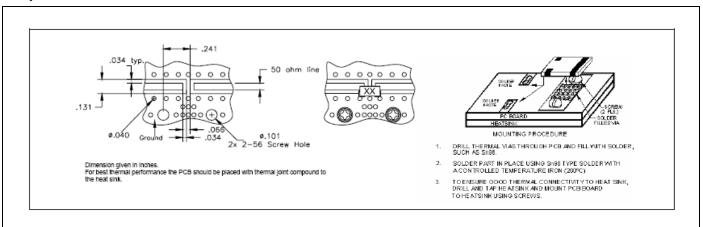
# **Power De-rating:**



## **Mounting Footprint:**



## Tape and Reel:



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